

## PLUS Search Results for S/N 10689792, Searched February 21, 2006

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**Titles of Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10689792 on February 21, 2006**

5 438/624 (2 OR, 3 XR)  
 Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL  
 438/597 .To form ohmic contact to semiconductive material  
 438/618 ..Contacting multiple semiconductive regions (i.e., interconnects)  
 438/622 ...Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)  
 438/624 ....Separating insulating layer is laminate or composite of plural insulating materials

4 428/433 (0 OR, 4 XR)  
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
 428/426 .Of quartz or glass  
 428/432 ..Next to metal or compound thereof  
 428/433 ...Alloy or free metal

4 428/461 (1 OR, 3 XR)  
 Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
 428/457 .Of metal  
 428/461 ..Next to addition polymer from unsaturated monomers

4 438/637 (0 OR, 4 XR)  
 Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL  
 438/597 .To form ohmic contact to semiconductive material  
 438/618 ..Contacting multiple semiconductive regions (i.e., interconnects)  
 438/622 ...Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)  
 438/637 ....With formation of opening (i.e., viahole) in insulative layer

3 257/758 (1 OR, 2 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
 257/741 .Of specified material other than unalloyed aluminum  
 257/750 ..Layered  
 257/758 ...Multiple metal levels on semiconductor, separated by insulating layer (e.g., multiple level metallization for integrated circuit)

3 257/E21.162 (0 OR, 3 XR)  
 Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor

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device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without impurities, e.g., doping materials (EPO)

257/E21.158 ....Manufacture of electrode on semiconductor body using process other than by epitaxial growth, diffusion of impurities, alloying of impurity materials, or radiation bombardment (EPO)

257/E21.159 .....Deposition of conductive or insulating material for electrode conducting electric current (EPO)

257/E21.16 .....From a gas or vapor, e.g., condensation (EPO)

257/E21.161 .....Of conductive layer (EPO)

257/E21.162 .....On semiconductor body comprising Group IV element (EPO)

3 257/E21.245 (0 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES  
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE

DEVICES OR OF

257/E21.002 .Manufacture or treatment of semiconductor device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without impurities, e.g., doping materials (EPO)

257/E21.211 ....Treatment of semiconductor body using process other than deposition of semiconductor material on a substrate, diffusion or alloying of impurity material, or radiation treatment (EPO)

257/E21.214 .....To change their surface-physical characteristics or shape, e.g., etching, polishing, cutting (EPO)

257/E21.24 .....To form insulating layer thereon, e.g., for masking or by using photolithographic technique (EPO)

257/E21.241 .....Post-treatment (EPO)

257/E21.243 .....Planarization of insulating layer (EPO)

257/E21.244 .....Involving dielectric removal step (EPO)

257/E21.245 .....Removal by chemical etching, e.g., dry etching (EPO)

3 257/E21.266 (0 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion

layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without

impurities, e.g., doping materials (EPO)

257/E21.211 ....Treatment of semiconductor body using process other than deposition of semiconductor material on

a substrate, diffusion or alloying of impurity material, or

radiation treatment (EPO)

257/E21.214 .....To change their surface-physical characteristics or shape, e.g., etching, polishing, cutting

(EPO)

257/E21.24 .....To form insulating layer thereon, e.g., for masking or by using photolithographic technique (EPO)

257/E21.266 ....Inorganic layer (EPO)

3 257/E21.295 (0 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF

PARTS THEREOF (EPO)

257/E21.002 .Manufacture or treatment of semiconductor device (EPO)

257/E21.04 ..Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion

layer, carrier concentration layer (EPO)

257/E21.085 ...Device having semiconductor body comprising Group IV elements or Group III-V compounds with or without

impurities, e.g., doping materials (EPO)

257/E21.211 ....Treatment of semiconductor body using process other than deposition of semiconductor material on

a substrate, diffusion or alloying of impurity material, or

radiation treatment (EPO)

257/E21.214 .....To change their surface-physical characteristics or shape, e.g., etching, polishing, cutting

(EPO)

257/E21.294 ....Deposition/post-treatment of noninsulating, e.g., conductive - or resistive - layers on

insulating layers (EPO)

257/E21.295 ....Deposition of layer comprising metal, e.g., metal, alloys, metal compounds (EPO)

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3 257/E21.58 (0 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/E21.531 ...For electrical parameters, e.g.,  
resistance, deep-levels, CV, diffusions by  
electrical means  
(EPO)  
257/E21.532 .Manufacture or treatment of devices  
consisting of plurality of solid-state components  
formed in  
manufacture of  
integrated circuit devices or of parts thereof (EPO)  
257/E21.536 ..Manufacture of specific parts of devices  
(EPO)  
257/E21.575 ...Interconnections, comprising conductors and  
dielectrics, for carrying current between separate  
components within device (EPO)  
257/E21.576 ....Characterized by formation and post  
treatment of dielectrics, e.g., planarizing (EPO)  
257/E21.58 ....Planarizing dielectric (EPO)

3 257/E23.145 (0 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/E23.139 ...Liquid at normal operating temperature of  
device (EPO)  
257/E23.141 .Arrangements for conducting electric current  
within device in operation from one component to  
another,  
interconnections, e.g., wires, lead frames (EPO)  
257/E23.142 ..Including external interconnections  
consisting of multilayer structure of conductive and  
insulating layers inseparably formed on semiconductor  
body  
(EPO)  
257/E23.145 ...Via connections in multilevel  
interconnection structure (EPO)

3 428/209 (0 OR, 3 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)  
428/195.1 .Discontinuous or differential coating,  
impregnation or bond (e.g., artwork, printing, retouched  
photograph, etc.)  
428/209 ..Including metal layer

3 428/35.9 (1 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/34.1 HOLLOW OR CONTAINER TYPE ARTICLE (E.G., TUBE,  
VASE, ETC.)  
428/35.7 .Polymer or resin containing (i.e., natural or  
synthetic)  
428/35.8 ..Elemental metal containing (e.g., substrate,  
foil, film, coating, etc.)  
428/35.9 ....Three or more layers (continuous layer)

2 117/108 (0 OR, 2 XR)  
Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY  
GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR  
117/84 FORMING FROM VAPOR OR GASEOUS STATE (E.G., VPE,  
SUBLIMATION)  
117/108 .Using an energy beam or field, a particle beam  
or field, or a plasma (e.g., MBE)

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2 117/940 (0 OR, 2 XR)  
Class 117 : SINGLE-CRYSTAL, ORIENTED-CRYSTAL, AND EPITAXY  
GROWTH PROCESSES; NON-COATING APPARATUS THEREFOR  
117/937 INORGANIC CONTAINING SINGLE-CRYSTAL (E.G.,  
COMPOUND, MIXTURE, COMPOSITE) {C30B 29/10}  
117/940 .Halide containing (e.g., fluorophlogopite,  
fluor-mica) {C30B 29/12}

2 118/308 (0 OR, 2 XR)  
Class 118 : COATING APPARATUS  
118/300 PROJECTION OR SPRAY TYPE  
118/308 .Applying solid particulate material

2 118/323 (0 OR, 2 XR)  
Class 118 : COATING APPARATUS  
118/300 PROJECTION OR SPRAY TYPE  
118/323 .Moving projector

2 118/59 (1 OR, 1 XR)  
Class 118 : COATING APPARATUS  
118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS  
OR VAPOR TREATMENT OF WORK  
118/59 .With solid heat exchange means contacting work

2 118/673 (0 OR, 2 XR)  
Class 118 : COATING APPARATUS  
118/663 CONTROL MEANS RESPONSIVE TO A RANDOMLY  
OCCURRING SENSED CONDITION  
118/668 .Responsive to attribute, absence or presence  
of work  
118/672 ..Running length work  
118/673 ...Edge of running length of web material  
sensed

2 118/69 (0 OR, 2 XR)  
Class 118 : COATING APPARATUS  
118/58 WITH HEAT EXCHANGE, DRYING, OR NON-COATING GAS  
OR VAPOR TREATMENT OF WORK  
118/69 .Cooling

2 148/33.4 (1 OR, 1 XR)  
Class 148 : METAL TREATMENT  
148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE  
148/33.4 .With contiguous layers of different  
semiconductive material

2 148/33.5 (0 OR, 2 XR)  
Class 148 : METAL TREATMENT  
148/33 BARRIER LAYER STOCK MATERIAL, P-N TYPE  
148/33.5 .Having at least three contiguous layers of  
semiconductive material

2 216/13 (1 OR, 1 XR)  
Class 216 : ETCHING A SUBSTRATE: PROCESSES  
216/13 FORMING OR TREATING ELECTRICAL CONDUCTOR  
ARTICLE (E.G., CIRCUIT, ETC.)

2 220/62.12 (2 OR, 0 XR)  
Class 220 : RECEPTACLES  
220/62.11 RECEPTACLE SIDE WALL MADE OF TWO OR MORE LAYERS  
OF MATERIAL PERMANENTLY ATTACHED TOGETHER

10689792\_CLSTITLES1.txt

220/62.12 .Beverage receptacle

2 220/669 (0 OR, 2 XR)  
Class 220 : RECEP TACLES  
220/660 SIDEWALL STRUCTURE  
220/669 .Contoured sidewall (e.g., curved, corrugated, ribbed, variable thickness, etc.)

2 228/121 (1 OR, 1 XR)  
Class 228 : METAL FUSION BONDING  
228/101 PROCESS  
228/121 .Bonding nonmetals with metallic filler

2 228/122.1 (0 OR, 2 XR)  
Class 228 : METAL FUSION BONDING  
228/101 PROCESS  
228/122.1 .Metal to nonmetal with separate metallic filler

2 228/124.1 (0 OR, 2 XR)  
Class 228 : METAL FUSION BONDING  
228/101 PROCESS  
228/122.1 .Metal to nonmetal with separate metallic filler  
228/124.1 ..With treating

2 228/195 (1 OR, 1 XR)  
Class 228 : METAL FUSION BONDING  
228/101 PROCESS  
228/193 .Diffusion type  
228/195 ..With incipient melting of bonding surface

2 257/750 (0 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed aluminum  
257/750 ..Layered

2 257/751 (0 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed aluminum  
257/750 ..Layered  
257/751 ...At least one layer forms a diffusion barrier

2 257/761 (0 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed aluminum  
257/750 ..Layered  
257/761 ...At least one layer containing vanadium, hafnium, niobium, zirconium, or tantalum

2 257/769 (0 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD  
257/741 .Of specified material other than unalloyed aluminum  
257/768 ..Refractory or platinum group metal or alloy

257/769 ...Platinum group metal or silicide thereof

2 257/E21.585 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,  
resistance, deep-levels, CV, diffusions by  
electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices  
consisting of plurality of solid-state components

formed in

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices  
(EPO)257/E21.575 ...Interconnections, comprising conductors and  
dielectrics, for carrying current between separate  
components within device (EPO)257/E21.576 ....Characterized by formation and post  
treatment of dielectrics, e.g., planarizing (EPO)257/E21.585 .....Filling of holes, grooves, vias or  
trenches with conductive material (EPO)

2 257/E21.59 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E21.531 ...For electrical parameters, e.g.,  
resistance, deep-levels, CV, diffusions by

electrical means

(EPO)

257/E21.532 .Manufacture or treatment of devices  
consisting of plurality of solid-state components

formed in

manufacture of

integrated circuit devices or of parts thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices  
(EPO)257/E21.575 ...Interconnections, comprising conductors and  
dielectrics, for carrying current between separate  
components within device (EPO)257/E21.576 ....Characterized by formation and post  
treatment of dielectrics, e.g., planarizing (EPO)

257/E21.59 .....Local interconnects; local pads (EPO)

2 257/E23.106 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.079 ..For integrated circuit devices, e.g., power  
bus, number of leads (EPO)257/E23.08 .Arrangements for cooling, heating, ventilating  
or temperature compensation; temperature-sensing  
arrangements (EPO)257/E23.101 ..Selection of materials, or shaping, to  
facilitate cooling or heating, e.g., heat sinks (EPO)257/E23.106 ...Laminates or multilayers, e.g., direct bond  
copper ceramic substrates (EPO)

2 257/E23.147 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.139 ...Liquid at normal operating temperature of  
device (EPO)

257/E23.141 .Arrangements for conducting electric current

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within device in operation from one component to

another,

257/E23.142 ..Including external interconnections  
consisting of multilayer structure of conductive and  
insulating layers inseparably formed on semiconductor

body

(EPO)

257/E23.146 ...With adaptable interconnections (EPO)

257/E23.147 ....Comprising antifuses, i.e., connections  
having their state changed from nonconductive to

conductive

(EPO)

2 257/E23.167 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E23.139 ...Liquid at normal operating temperature of  
device (EPO)

257/E23.141 .Arrangements for conducting electric current  
within device in operation from one component to

another,

interconnections, e.g., wires, lead frames (EPO)

257/E23.142 ..Including external interconnections  
consisting of multilayer structure of conductive and  
insulating layers inseparably formed on semiconductor

body

(EPO)

257/E23.154 ...Characterized by materials (EPO)

257/E23.167 ....Insulating materials (EPO)

2 257/E29.162 (0 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E29.104 ...Si compounds (e.g., SiC) (EPO)

257/E29.111 .Electrodes (EPO)

257/E29.139 ..Of specified material (EPO)

257/E29.15 ...Electrodes for IGFET (EPO)

257/E29.162 ....Insulating materials for IGFET (EPO)

2 359/586 (0 OR, 2 XR)

Class 359 : OPTICS: SYSTEMS

359/577 LIGHT INTERFERENCE

359/580 .Produced by coating or lamina

359/586 ..Layers having specified index of refraction

2 427/422 (0 OR, 2 XR)

Class 427 : COATING PROCESSES

427/421.1 SPRAYING

427/422 .Heated coating material

2 427/424 (0 OR, 2 XR)

Class 427 : COATING PROCESSES

427/421.1 SPRAYING

427/424 .Moving the base

2 427/446 (1 OR, 1 XR)

Class 427 : COATING PROCESSES

427/446 SPRAY COATING UTILIZING FLAME OR PLASMA HEAT  
(E.G., FLAME SPRAYING, ETC.)

2 428/210 (2 OR, 0 XR)

Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES

428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
Page 8

10689792\_CLSTITLES1.txt  
OVERALL DIMENSION, ETC.)

428/195.1 .Discontinuous or differential coating,  
impregnation or bond (e.g., artwork, printing, retouched  
photograph, etc.)

428/210 ..Including ceramic, glass, porcelain or quartz  
layer

2 428/213 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)

428/212 .Including components having same physical  
characteristic in differing degree

428/213 ..Thickness (relative or absolute)

2 428/214 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)

428/212 .Including components having same physical  
characteristic in differing degree

428/213 ..Thickness (relative or absolute)

428/214 ...Of adhesive layers

2 428/215 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/98 STRUCTURALLY DEFINED WEB OR SHEET (E.G.,  
OVERALL DIMENSION, ETC.)

428/212 .Including components having same physical  
characteristic in differing degree

428/213 ..Thickness (relative or absolute)

428/215 ...Absolute thicknesses specified

2 428/457 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
428/457 .of metal

2 428/462 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/411.1 COMPOSITE (NONSTRUCTURAL LAMINATE)  
428/457 .of metal  
428/461 ..Next to addition polymer from unsaturated  
monomers  
428/462 ...Including polyene monomers (e.g., butadiene,  
etc.)

2 428/623 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)

428/621 ..with additional, spatially distinct nonmetal  
component

428/622 ...More than one such component

428/623 ....Adjacent to each other

2 428/627 (1 OR, 1 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)

428/621 ..with additional, spatially distinct nonmetal

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component  
428/627 ...Boride, carbide or nitride component

2 428/654 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/544 ALL METAL OR WITH ADJACENT METALS  
428/615 .Composite; i.e., plural, adjacent, spatially  
distinct metal components (e.g., layers, joint, etc.)  
428/650 ..Al-base component  
428/654 ...Next to Al-base component

2 428/901 (0 OR, 2 XR)  
Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/901 PRINTED CIRCUIT

2 438/622 (1 OR, 1 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/618 ..Contacting multiple semiconductive regions  
(i.e., interconnects)  
438/622 ...Multiple metal levels, separated by  
insulating layer (i.e., multiple level metallization)

2 438/675 (1 OR, 1 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/584 COATING WITH ELECTRICALLY OR THERMALLY  
CONDUCTIVE MATERIAL  
438/597 .To form ohmic contact to semiconductive  
material  
438/674 ..Selective deposition of conductive layer  
438/675 ...Plug formation (i.e., in viahole)

2 438/699 (0 OR, 2 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/689 CHEMICAL ETCHING  
438/694 .Combined with coating step  
438/697 ..Planarization by etching and coating  
438/699 ...Plural coating steps

2 438/763 (0 OR, 2 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/758 COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR  
REGION OR OF SEMICONDUCTOR SUBSTRATE  
438/761 ..Multiple layers  
438/763 ..Layers formed of diverse composition or by  
diverse coating processes

10689792\_CLS1.txt

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10689792 on February 21, 2006

Original Classifications

2 220/62.12  
2 428/210  
2 438/624

Cross-Reference Classifications

4 428/433  
4 438/637  
3 257/E21.162  
3 257/E21.245  
3 257/E21.266  
3 257/E21.295  
3 257/E21.58  
3 257/E23.145  
3 428/209  
3 428/461  
3 438/624  
2 117/108  
2 117/940  
2 118/308  
2 118/323  
2 118/673  
2 118/69  
2 148/33.5  
2 220/669  
2 228/122.1  
2 228/124.1  
2 257/750  
2 257/751  
2 257/758  
2 257/761  
2 257/769  
2 257/E21.585  
2 257/E21.59  
2 257/E23.106  
2 257/E23.147  
2 257/E23.167  
2 257/E29.162  
2 359/586  
2 427/422  
2 427/424  
2 428/213  
2 428/214  
2 428/35.9  
2 428/457  
2 428/462  
2 428/654  
2 428/901  
2 438/699  
2 438/763

Combined Classifications

5 438/624  
4 428/433  
4 428/461  
4 438/637  
3 257/758  
3 257/E21.162  
3 257/E21.245

10689792\_CLS1.txt

3 257/E21.266  
3 257/E21.295  
3 257/E21.58  
3 257/E23.145  
3 428/209  
3 428/35.9  
2 117/108  
2 117/940  
2 118/308  
2 118/323  
2 118/59  
2 118/673  
2 118/69  
2 148/33.4  
2 148/33.5  
2 216/13  
2 220/62.12  
2 220/669  
2 228/121  
2 228/122.1  
2 228/124.1  
2 228/195  
2 257/750  
2 257/751  
2 257/761  
2 257/769  
2 257/E21.585  
2 257/E21.59  
2 257/E23.106  
2 257/E23.147  
2 257/E23.167  
2 257/E29.162  
2 359/586  
2 427/422  
2 427/424  
2 427/446  
2 428/210  
2 428/213  
2 428/214  
2 428/215  
2 428/457  
2 428/462  
2 428/623  
2 428/627  
2 428/654  
2 428/901  
2 438/622  
2 438/675  
2 438/699  
2 438/763